

**IN THE CLAIMS**

Please amend the following claims.

1-29 (cancelled)

30. (currently amended) A method of forming a semiconductor device comprising:

forming a gate electrode having a first thickness on a gate dielectric layer formed on a substrate;

forming a pair of source/drain regions on opposite sides of the gate electrode;

forming a ~~silicon-germanium~~ semiconductor material film having a second thickness on the gate electrode and on the source/drain regions;

~~forming a silicon-germanium film having the second thickness on the source/drain regions~~;

forming a silicide layer having a third thickness on the ~~silicon-germanium films~~ semiconductor material film, the third thickness at least twice a sum of the first thickness and the second thickness; and

forming a pair of sidewall spacers having a height above the third thickness of the silicide layer on the ~~silicon-germanium~~ semiconductor material film on the gate electrode.

31. (cancelled)

32. (previously presented) The method of claim 30, wherein the sidewall spacers comprise silicon nitride.

33. (cancelled)

34. (cancelled)

35. (cancelled)

36. (previously presented) The method of claim 30 wherein the gate electrode comprises polysilicon.

37. (previously presented) The method of claim 30 wherein the sidewall spacers are less than 300Å in width.